10. (Original) The semiconductor in claim 9, wherein said dopant is included in a peak concentration of approximately 1×10^{20} cm^3 to 1×10^{21} cm^3.

11. (Original) The semiconductor in claim 9, wherein said dopant comprises one of boron, aluminum, gallium, indium, and titanium.

12. (Original) The semiconductor in claim 9, further comprising silicon germanium.

13. (Original) The semiconductor in claim 9, wherein said carbon atoms maintain said dopant within a central portion of said semiconductor.

14. (Original) A method of forming a bipolar transistor comprising:

forming a collector region in a wafer;

growing an epitaxial layer having carbon on said wafer, wherein said epitaxial layer has a semiconductor region above said collector region;

forming an emitter on said semiconductor region, wherein said emitter includes an insulator portion; and

doping said semiconductor region in sufficient quantities to reduce a resistance of said semiconductor to less than approximately 4 Kohms/cm^2,

wherein said carbon limits outdiffusion of said dopant within said semiconductor region.

15. (Original) The method in claim 15, wherein said doping provides said dopant in a peak concentration of approximately 1×10^{20} cm^3 to 1×10^{21} cm^3.

16. (Original) The method in claim 15, wherein said dopant comprises one of boron, aluminum, gallium, indium, and titanium.

17. (Original) The method in claim 15, wherein said semiconductor region further comprises silicon germanium.

18. (Original) The method in claim 15, wherein said carbon maintains said dopant within a central portion of said semiconductor region.

19. (Original) The method in claim 15, wherein said growing of said epitaxial layer includes growing a material including a concentration of carbon which is less than approximately 3%.